

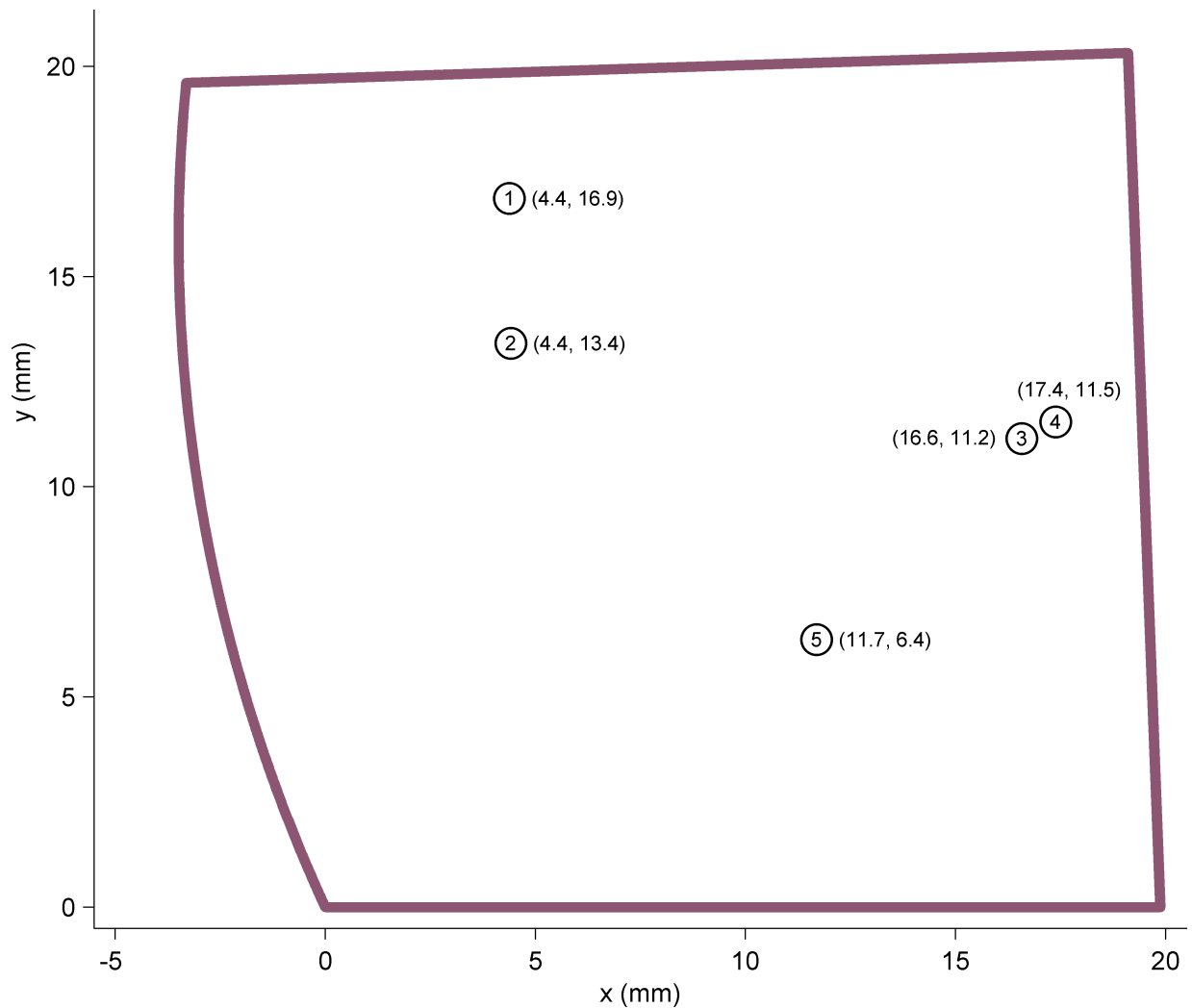


Sample S5512 Datasheet

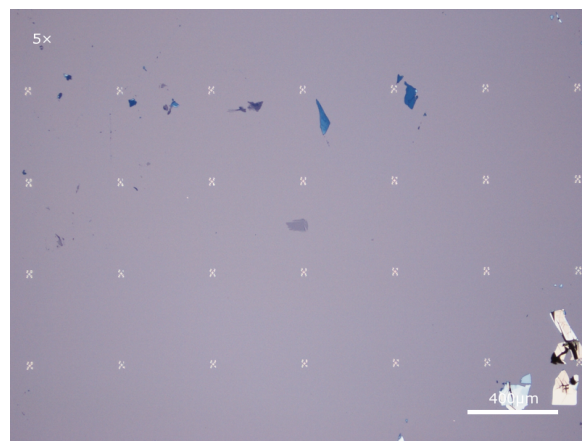
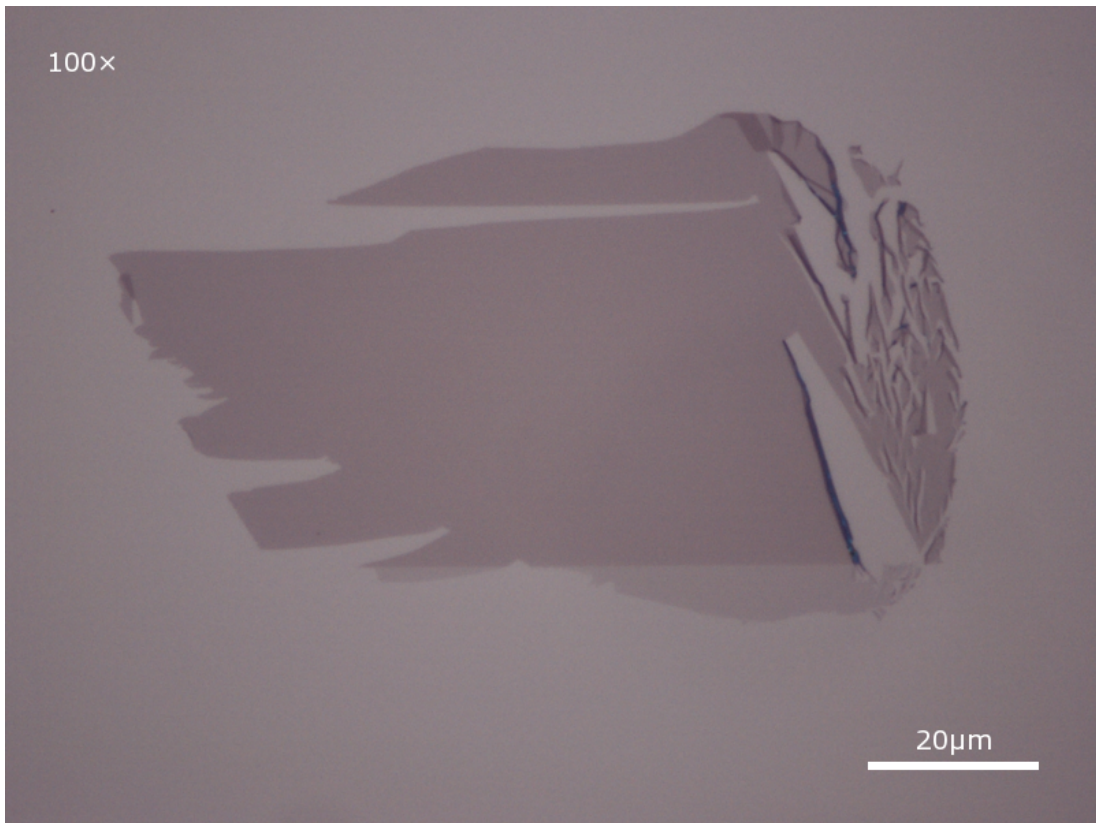
Parent Wafer

Supplier	IDB Technologies Ltd.
Diameter	100mm
Si Orientation	<100>
Si Thickness	525 μm
Si Doping	N-type, arsenic
Resistivity	0.001-0.010 Ωcm
Oxide	90 nm dry thermal oxide

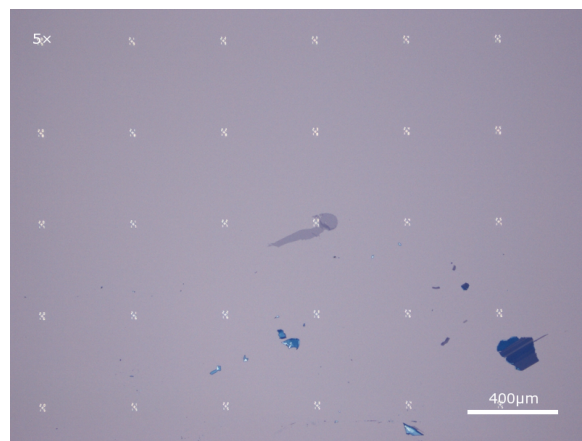
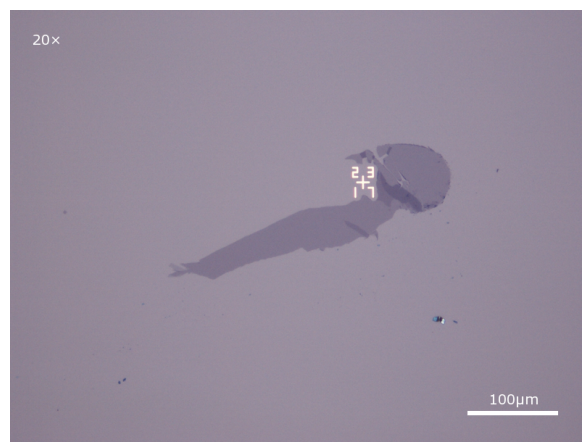
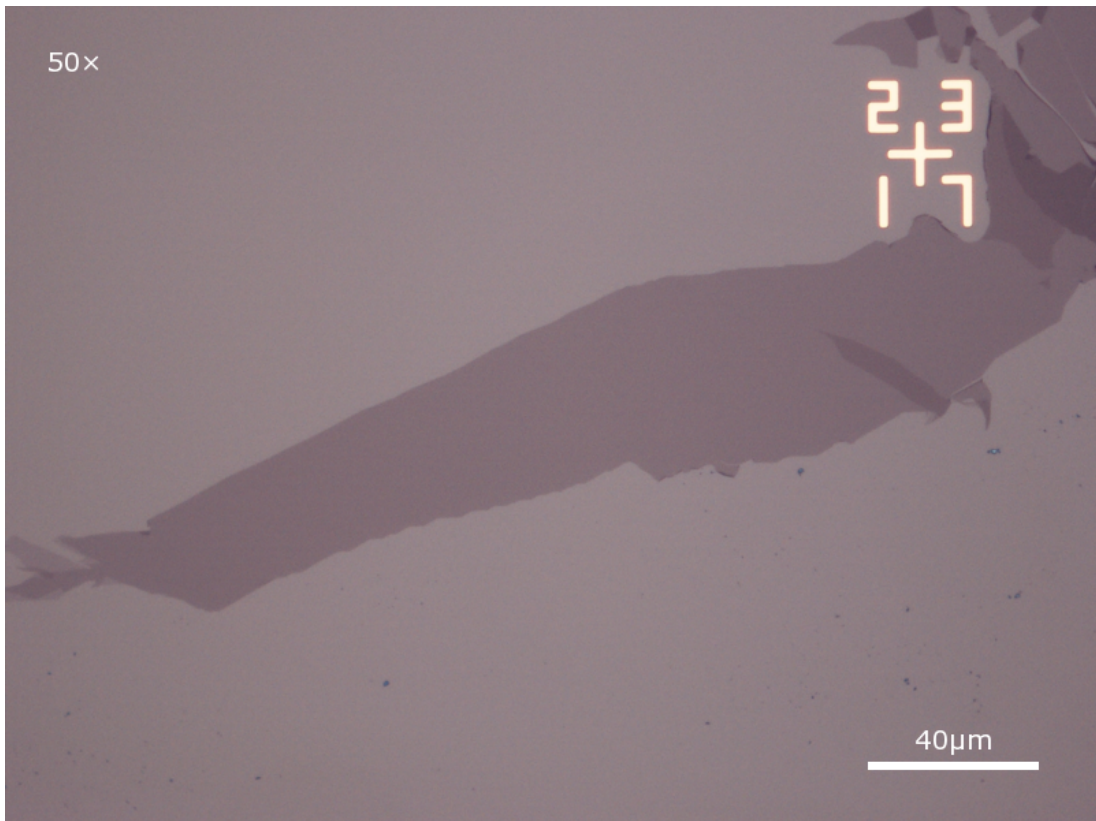
Substrate Map



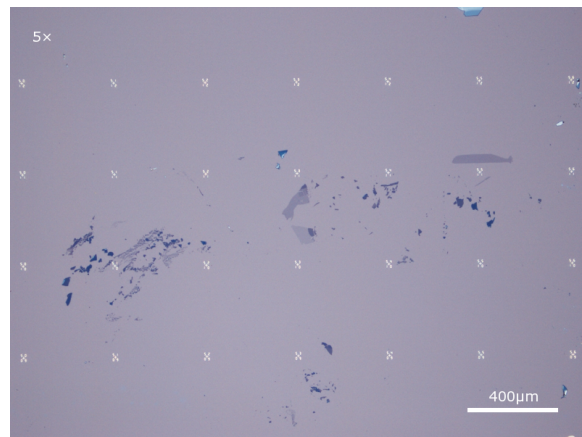
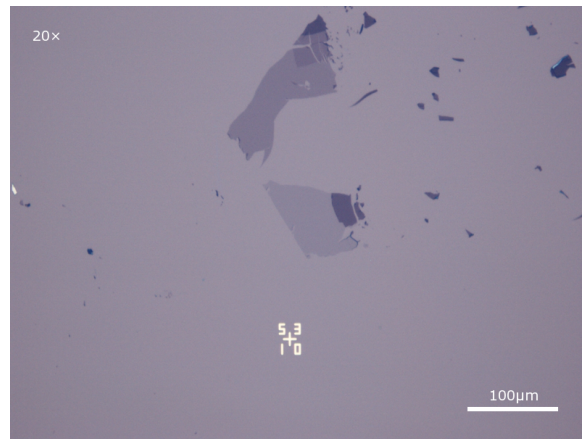
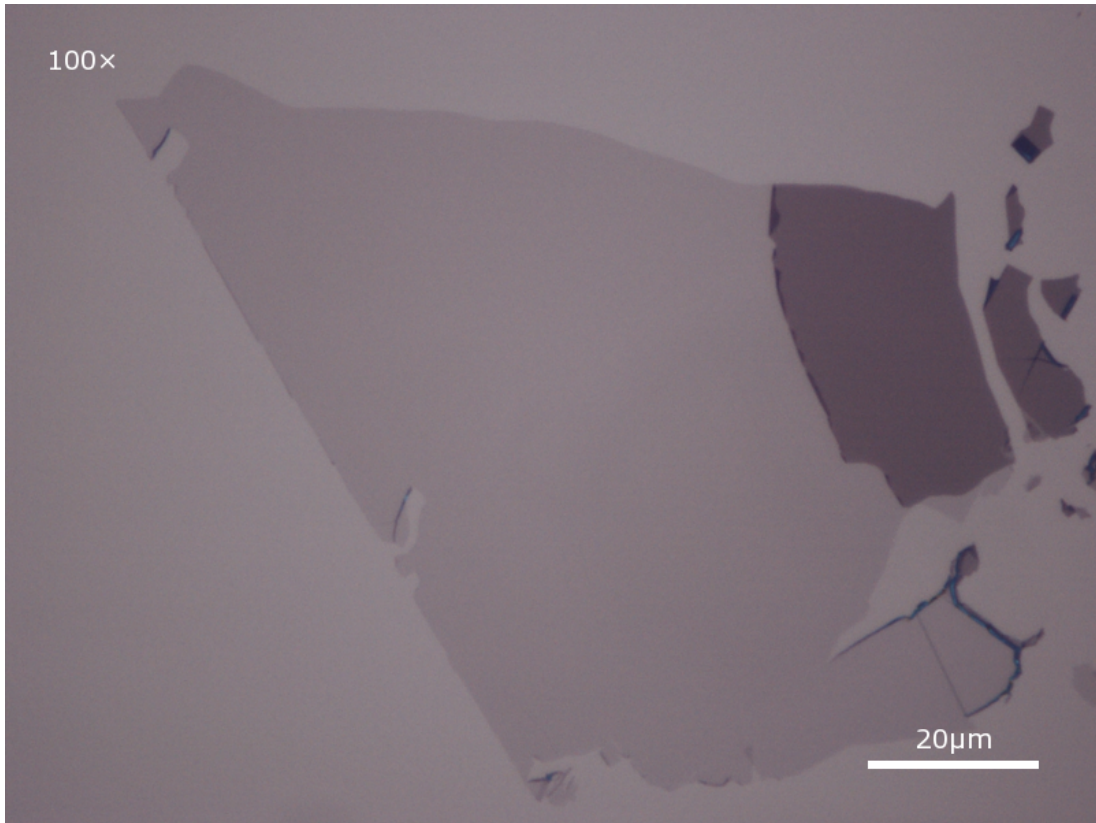
Flake 1 of 5: x=4.4mm, y=16.9mm, >2000 μm^2 bilayer region



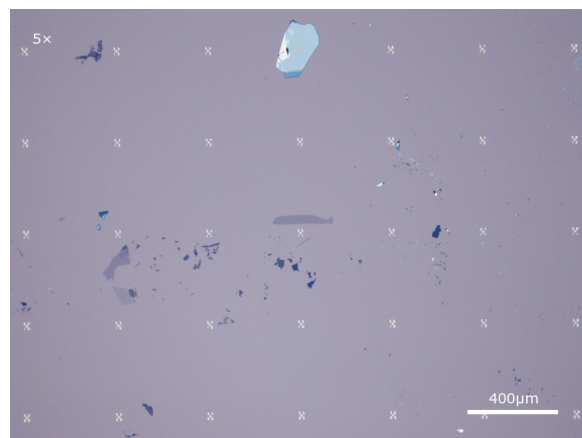
Flake 2 of 5: x=4.4mm, y=13.4mm, >5000 μm^2 bilayer region



Flake 3 of 5: $x=16.6\text{mm}$, $y=11.2\text{mm}$, $>3500\ \mu\text{m}^2$ monolayer region



Flake 4 of 5: x=17.4mm, y=11.5mm, >6000 μm^2 bilayer flake



Flake 5 of 5: $x=11.7\text{mm}$, $y=6.4\text{mm}$, $>500\ \mu\text{m}^2$ mono- and $>2000\ \mu\text{m}^2$ bilayer regions

